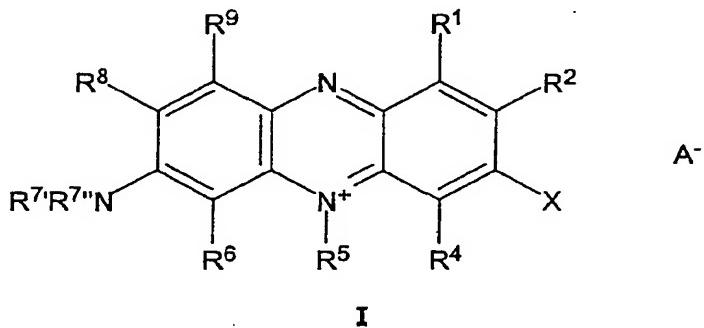


AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of all claims in the application.

LISTING OF THE CLAIMS

Claim 1. (Currently amended) Halogenated or pseudohalogenated monomeric phenazinium compounds of a purity of at least 85 mole-% having the following general chemical formula I:



wherein R¹, R², R⁴, R⁶, R⁷, R^{7''}, R⁸ and R⁹ are selected independently of each other from a group consisting of comprising hydrogen, halogen, amino, aminoalkyl, hydroxy, cyano, thiocyanate, isothiocyanate, cyanate, isocyanate, mercapto, carboxy, the salt thereof, carbonic acid ester, sulfo, the salt thereof, sulfoester, lower alkyl, unsubstituted aryl, substituted aryl, heteroaryl and alicyclic heteroradicals, R⁵ is selected from a group consisting of comprising lower alkyl, unsubstituted aryl, substituted aryl and heteroaryl, X is a halogen or a pseudohalogen and A⁻ is an acid anion.

Claim 2. (Currently Amended) The phenazinium compounds according to claim 1, characterized in that R¹, R², R⁴, R⁶, R^{7'}, R^{7"}, R⁸ and R⁹ are selected independently of each other from a group consisting of comprising hydrogen and lower alkyl.

Claim 3.(Original) The phenazinium compounds according to claim 2, characterized in that lower alkyl is methyl or ethyl.

Claim 4. (Currently Amended) The phenazinium compounds according to claim 1 any one of the preceding claims, characterized in that R⁵ is aryl.

Claim 5. (Original) The phenazinium compounds according to claim 4, characterized in that aryl is phenyl.

Claim 6. (Currently Amended) The phenazinium compounds according to claim 1 any one of the preceding claims, characterized in that X is chlorine, bromine or thiocyanate.

Claim 7. (Currently Amended) The phenazinium compounds according to claim 1 any one of the preceding claims, characterized in that they are selected from a group comprising i) 3-chloro-7-N, N-dimethylamino-2-methyl-5-phenyl-phenazinium salt, ii) 3-bromo-7-N,N-dimethylamino-2-methyl-5-phenyl-phenazinium salt, iii) 3-bromo-7-N, N-diethylamino-5-phenyl-phenazinium salt and iv) 7-amino-2,8-dimethyl-3-thiocyanato-5-phenyl-phenazinium salt.

Claim 8. (Currently Amended) The phenazinium compounds according to claim 7, characterized in that the salt is selected from a group ~~comprising~~ consisting of chloride, bromide, hydrogen sulfate and tetrafluoroborate.

Claim 9. (Currently Amended) The phenazinium compounds according to claim 7 any one of claims 7 and 8, characterized in that they are selected from a group ~~comprising~~ consisting of i) 3-chloro-7-N, N-dimethylamino-2-methyl-5-phenyl-phenazinium chloride, ii) 3-bromo-7-N,N-dimethylamino-2-methyl-5-phenyl-phenazinium bromide, iii) 3-bromo-7-N, N-diethylamino-5-phenyl-phenazinium bromide and iv) 7-amino-2, 8-dimethyl-3-thiocyanato-5-phenyl-phenaziniumtetrafluoroborate.

Claim 10. (Currently Amended) The phenazinium compounds according to claim 1 any one of the preceding claims, obtainable according to the following method: a) forming a diazonium compound by diazotization of a monomeric phenazinium compound comprising at least one primary amino group in the presence of mineral acid and diazotization means in a first reaction step, b) reacting the diazonium compound in a second reaction step to the halogenated or pseudohalogenated monomeric phenazinium compound in the presence of mineral acid and halide or pseudohalide, wherein the first and the second reaction steps are both run in one single vessel.

Claim 11. (Currently Amended) A method of preparing the halogenated or pseudohalogenated monomeric phenazinium compounds in accordance with claim 1 one of claims 1-10, comprising the following reaction steps: a) forming a diazonium

compound by diazotization of a monomeric phenazinium compound comprising at least one primary amino group in the presence of mineral acid and diazotization means in a first reaction step, b) reacting the diazonium compound in a second reaction step to the halogenated or pseudohalogenated monomeric phenazinium compound in the presence of mineral acid and halide or pseudohalide, characterized in that the first and the second reaction steps are both run in one single vessel.

Claim 12. (Currently Amended) The method according to claim 11, characterized in that the mineral acid is selected from a group ~~comprising~~ consisting of hydrogen halides, sulfuric acid, tetrafluoroboric acid, hexafluorophosphoric acid, phosphoric acid and the mixtures thereof with the proviso that no hydrogen halide is used in the preparation of the pseudohalogenated monomeric phenazinium compounds.

Claim 13. (Currently Amended) The method according to claim 11 ~~any one of claims 11 and 12~~, characterized in that the diazotization means is metal nitrite or nitrosylsulfuric acid.

Claim 14. (Original) The method according to claim 13, characterized in that the metal nitrite is sodium nitrite.

Claim 15. (Currently Amended) The method according to claim 11 ~~any one of claims 11 and 14~~, characterized in that the halide is added in the form of hydrogen halide and/or in the form of a metal halide.

Claim 16. (Currently Amended) The method according to claim 15, characterized in that the metal halide is selected from a group comprising consisting of transition metal halides.

Claim 17. (Currently Amended) The method according to claim 16, characterized in that the transition metal halides are selected from a group comprising consisting copper (I) halides, copper (II) halides, nickel (II) halides and iron (II) halides.

Claim 18. (Currently Amended) The method according to claim 11 any one of claims 11-17, characterized in that the halide is selected from a group comprising consisting of fluoride, chloride and bromide.

Claim 19. (Currently Amended) The method according to claim 11 any one of claims 11-17, characterized in that the pseudohalide is selected from a group comprising consisting of cyanate (-OCN), thiocyanate (-SCN), isocyanate (-NCO) and isothiocyanate (-NCS).

Claim 20. (Currently Amended) The method according to claim 11 any one of claims 11-19, comprising the following method steps: i) mixing the monomeric phenazinium compounds, comprising at least one primary amino group, with the mineral acid, ii) next heating to a temperature above room temperature, iii) adding the halide or pseudohalide iv) adding the diazotization means.

Claim 21. (Original) The method according to claim 20, characterized in that, in the preparation of the halogenated monomeric phenazinium compounds, the mineral acid is hydrogen halide and step iii) is eliminated.

Claim 22. (Currently Amended) The method according to claim 11 any one of claims 11-24, characterized in that the following halogenated or pseudohalogenated monomeric phenazinium compounds are prepared: a)3-chloro-7-N, N-dimethylamino-2-methyl-5-phenyl-phenazinium chloride, b) 3-bromo-7-N,N-dimethylamino-2-methyl-5-phenyl-phenazinium bromide, c) 3-bromo-7-N, N-diethylamino-5-phenyl-phenazinium bromide, d) 7-amino-2, 8-dimethyl-3-thiocyanato-5-phenyl-phenaziniumtetrafluoroborate.

Claim 23. (Currently Amended) An acidic bath for electrolytically depositing a copper deposit, containing at least one halogenated or pseudohalogenated monomeric phenazinium compound in accordance with claim 1 any one of claims 1-10.

Claim 24. (Original) The bath according to claim 23, characterized in that the phenazinium compounds are contained in a concentration of from 0.00005-0. 1 g/l.

Claim 25. (Currently Amended) The bath according to claim 23 one any of claims 23 and 24, characterized in that it additionally contains compounds selected from a group comprising consisting of nitrogen- containing sulfur compounds and polymeric nitrogen compounds.

Claim 26. (Original) The bath according to claim 25, characterized in that the concentration of the nitrogen-containing sulfur compounds and the polymeric nitrogen compounds contained together in the bath is from 0.0001-0. 50 g/l.

Claim 27. (Currently Amended) Use of the bath according to claim 23 any one of claims 23-26 for depositing a mirror bright, leveled copper deposit for the purpose of producing decorative surfaces.

Claim 28. (Currently Amended) Use of the bath according to claim 23 any one of claims 23-26 for forming a copper deposit on printed circuit board material.

Claim 29. (Currently Amended) Use of the bath according to claim 23 any one of claims 23-26 for forming a copper deposit on semiconductor substrates.

Claim 30. (Currently Amended) A method of electrolytically depositing a copper deposit onto a workpiece by which the workpiece and at least one anode are contacted with the bath according to claim 23 one of claims 23-26, and a flow of electric current is generated between the workpiece and the anodes.